



SILICON TRANSISTOR ARRAY $\mu PA1453$

PNP SILICON POWER TRANSISTOR ARRAY HIGH SPEED SWITCHING USE INDUSTRIAL USE

DESCRIPTION

The μ PA1453 is PNP silicon epitaxial Power Transistor Array that built in 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- Easy mount by 0.1 inch of terminal interval.
- High hFE. LOW VCE(sat).
 hFE = 100 to 400 (at Ic = -2 A)
 VCE(sat) = -0.3 V MAX. (at Ic = -2 A)

ORDERING INFORMATION

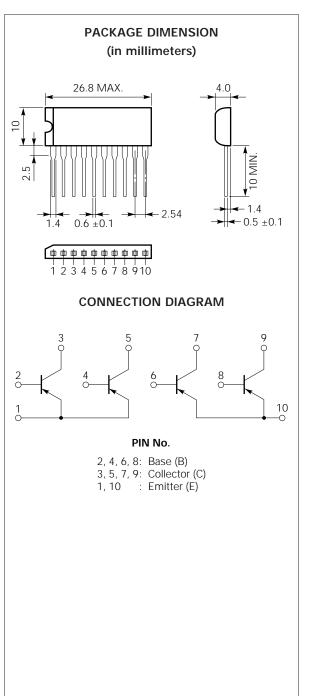
Part Number	Package	Quality Grade	
μΡΑ1453Η	10 Pin SIP	Standard	

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Collector to Base Voltage	Исво	-60	V
Collector to Emitter Voltage	Vceo	-60	V
Emitter to Base Voltage	Vebo	-7	V
Collector Current (DC)		-5	A/unit
Collector Current (pulse) IC(pulse)*		-10	A/unit
Base Current (DC)	B(DC)	-1.0	A/unit
Total Power Dissipation	PT1**	3.5	W
Total Power Dissipation	PT2***	28	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg –55	to +150	О°С

- * PW \leq 300 μ s, Duty Cycle \leq 10 %
- ** 4 Circuits, Ta = 25 °C
- *** 4 Circuits, Tc = 25 °C



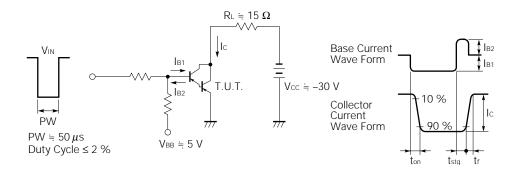
The information in this document is subject to change without notice.

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

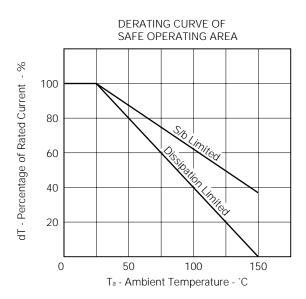
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Leakage Current	Ісво			-10	μA	$V_{CB} = -50 V, I_E = 0$	
Emitter Leakage Current	Іево			-10	μA	$V_{EB} = -5 V$, Ic = 0	
DC Current Gain	hfei *	60	220		_	$V_{CE} = -1 V$, $I_{C} = -0.1 A$	
DC Current Gain	hfe2 *	100	220	400	_	$V_{CE} = -1 V$, $I_{C} = -2 A$	
DC Current Gain	hfea *	50	100			$V_{CE} = -2 V$, $I_{C} = -5 A$	
Collector Saturation Voltage	V _{CE(sat)} *		-0.2	-0.3	V	$I_{C} = -2 A, I_{B} = -0.2 A$	
Base Saturation Voltage	V _{BE(sat)} *		-0.9	-1.2	V	$I_{C} = -2 A, I_{B} = -0.2 A$	
Turn On Time	ton			1	μs	Ic = -2 A	
Storage Time	tstg			2.5	μs	I _{B1} = −I _{B2} = −0.2 A Vcc ≒ −30 V, RL ≒ 15 Ω	
Fall Time	tr			1	μs	See test circuit	

* PW \leq 350 μ s, Duty Cycle \leq 2 % / pulsed

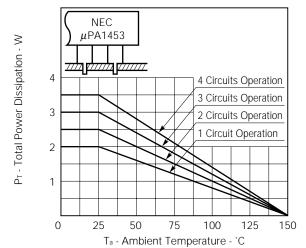
SWITCHING TIME TEST CIRCUIT

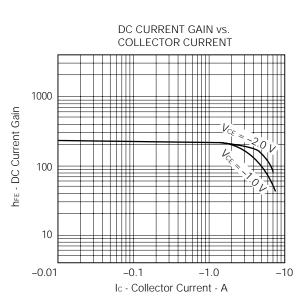


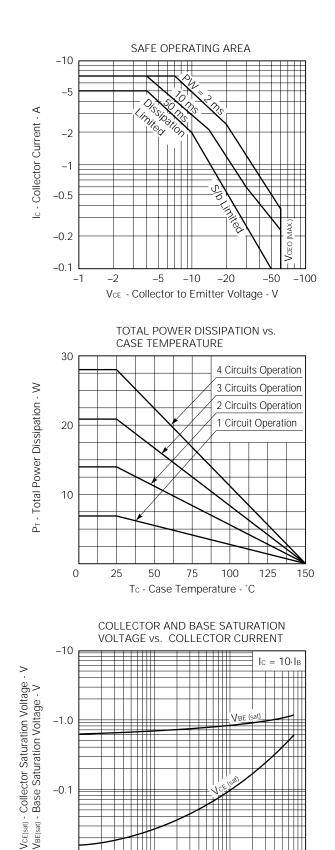
TYPICAL CHARACTERISTICS ($T_a = 25$ °C)











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+1

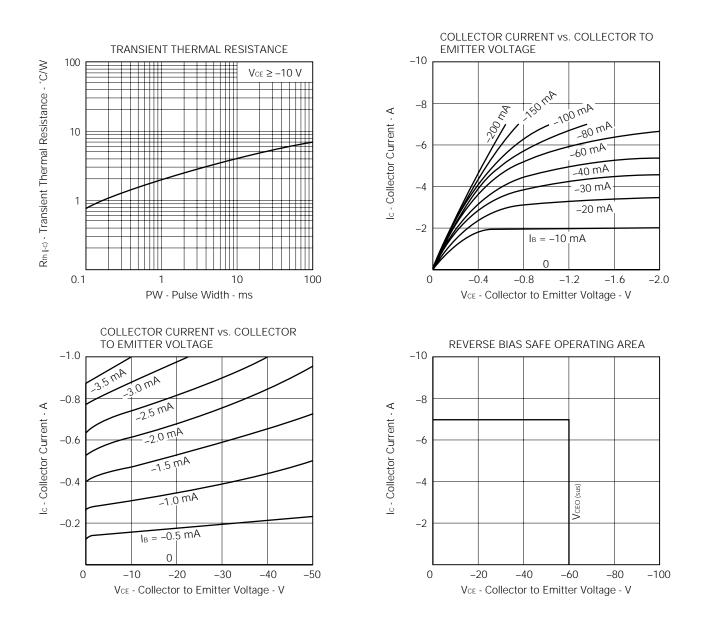
-0.1

Ic - Collector Current - A

-1.0

-0.01

-10



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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